

PRODUCT CHARACTERISTICS

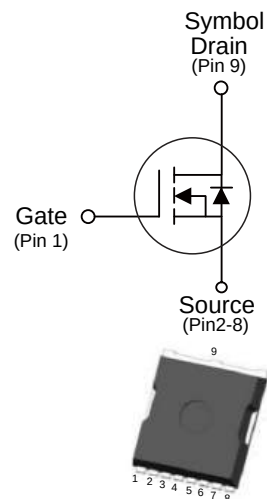
V_{DSS}	200V
$R_{DS(ON)} Typ(@V_{GS}=10V)$	9.5m Ω
$Q_g@typ$	87nc
I_D	100A

FEATURE

- * Uses MOT advanced double trench technology
- * Low On-Resistance ($R_{DS(on)} \leq 11.5m\Omega$)
- * Low Gate Charge
- * Low Reverse transfer capacitances
- * 100% avalanche tested
- * Pb-free plating; RoHS compliant

APPLICATIONS

- * Battery management
- * Motor control and drive
- * Synchronous rectification
- * Switching applications



TOLL



ORDER INFORMATION

Order Codes		Package	Packing
Halogen-Free	Halogen		
N/A	MOT9186T	TOLL	2000 pieces/Reel

ABSOLUTE MAXIMUM RATINGS($T_A=25^{\circ}C$, unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DSS}	200	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current Continuous($@V_{GS}=10V, T_A=25^{\circ}C$)	I_D	100	A
Drain Current Continuous($@V_{GS}=10V, T_A=100^{\circ}C$)	I_D	80	A
Drain Current Pulsed	I_{DM}	400	A
Avalanche Energy *	E_{AS}	1016	mJ
Power Dissipation	P_D	328	W
Junction Temperature	T_J	+150	$^{\circ}C$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}C$

THERMAL CHARACTERISTICS

Parameter	Symbol	Typ	Unit
Junction to Case	R_{thJC}	0.38	$^{\circ}C/W$

Note: * EAS condition: $T_J=25^{\circ}C, V_{DS}=50V, V_G=10V, L=0.5mH, R_g=25\Omega$

■ ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Off characteristics						
Drain to Source Breakdown Voltage	V _{DSS}	V _{GS} =0V,I _D =250μA	200	-	-	V
Drain to Source Leakage Current	I _{DSS}	V _{DS} =200V, V _{GS} =0V	-	-	1	μA
Gate to Source Forward Leakage	I _{GSS(F)}	V _{GS} =+20V, V _{DS} =0V	-	-	100	nA
Gate to Source Reverse Leakage	I _{GSS(R)}	V _{GS} =-20V , V _{DS} =0V	-	-	-100	nA
On characteristics						
Drain to Source On-Resistance	R _{DS(ON)}	V _{GS} =10V,I _D =20A	-	9.5	11.5	mΩ
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} ,I _D =250μA	2.0	3.4	4.0	V
Dynamic characteristics						
Gate capacitance	R _g	V _{GS} =0V,V _{DS} =0V ,f=1.0MHz	-	1.5	-	Ω
Forward Transconductance	g _{fs}	V _{DS} =10V,I _D =5A	10	-	-	S
Input Capacitance	C _{iss}	V _{DS} =25V,V _{GS} =0V f=1.0MHz	-	10900	-	pF
Output Capacitance	C _{oss}		-	2300	-	pF
Reverse Transfer Capacitance	C _{rss}		-	1300	-	pF
Resistive Switching Characteristics						
Turn-on Delay Time	t _{d(ON)}	V _{GS} =10V, V _{DS} =100V, I _D =50A ,R _G =4.7Ω	-	18	-	ns
Rise Time	t _r		-	26	-	ns
Turn-off Delay Time	t _{d(OFF)}		-	41	-	ns
Fall Time	t _f		-	11	-	ns
Total Gate Charge	Q _g	I _D =50A, V _{DS} =100V V _{GS} =10V	-	87	-	nC
Gate to Source Charge	Q _{gs}		-	32	-	nC
Gate to Drain("Miller") Charge	Q _{gd}		-	17.5	-	nC
Source-Drain Diode Characteristics						
Continuous Source Current(Body Diode)	I _S		-	-	100	A
Maximum Pulsed Current(Body Diode)	I _{SM}		-	-	400	A
Diode Forward Voltage	V _{SD}	I _{SD} =1A, V _{GS} =0V	-	0.67	1.2	V
Reverse Recovery Time	t _{rr}	I _{SD} =50A, T _J =25℃ dI/dt=100A/μs	-	140	-	ns
Reverse Recovery Charge	Q _{rr}		-	600	-	nC

■ TYPICAL CHARACTERISTICS

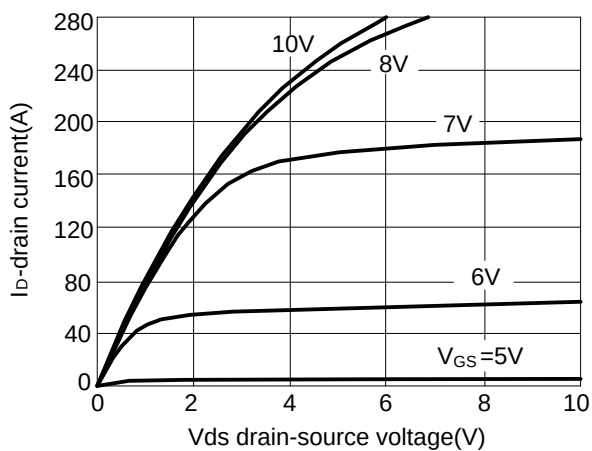


Figure 1: Output characteristics

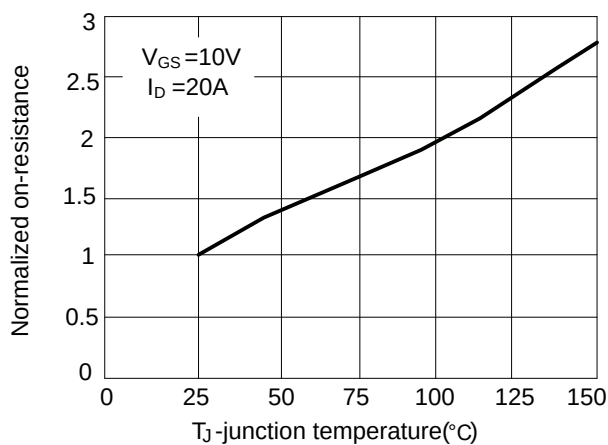


Figure 2: $R_{DS(on)}$ -junction temperature

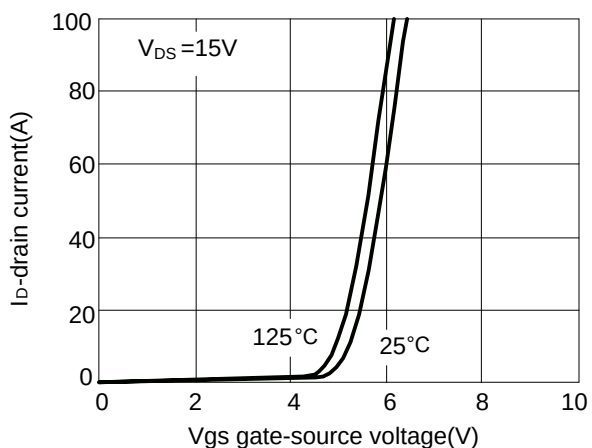


Figure 3: Transfer characteristics

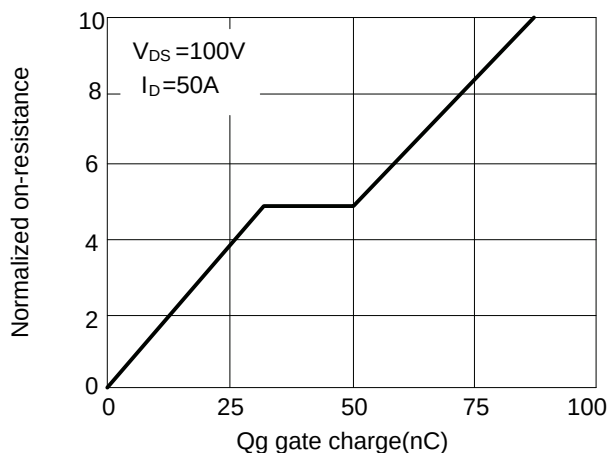


Figure 4: gate charge

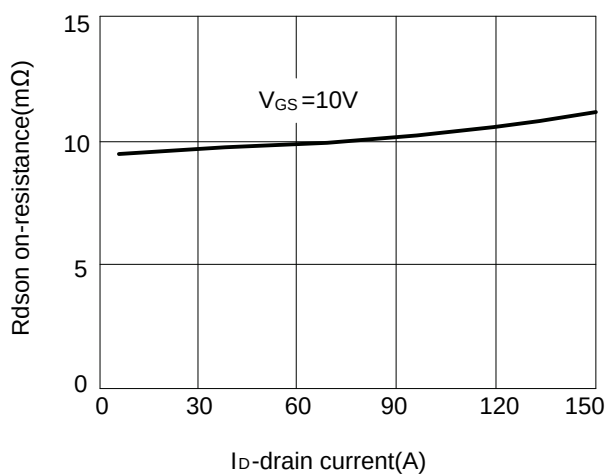


Figure 5: $R_{DS(on)}$ -drain current

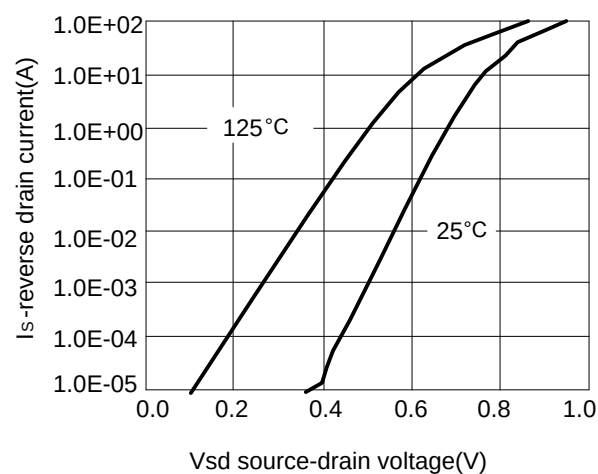


Figure 6: Source-drain diode forward

■ TYPICAL CHARACTERISTICS(Cont.)

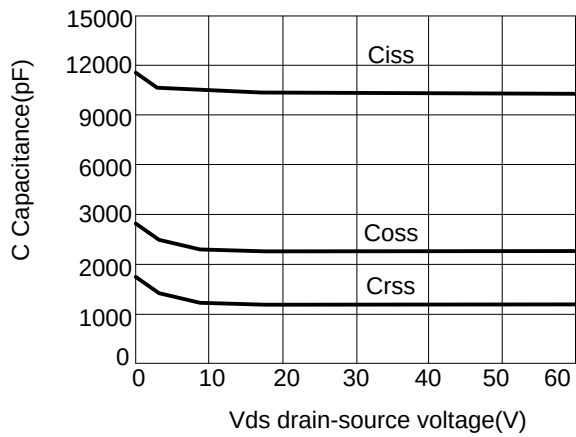


Figure 7: Capacitance vs vds

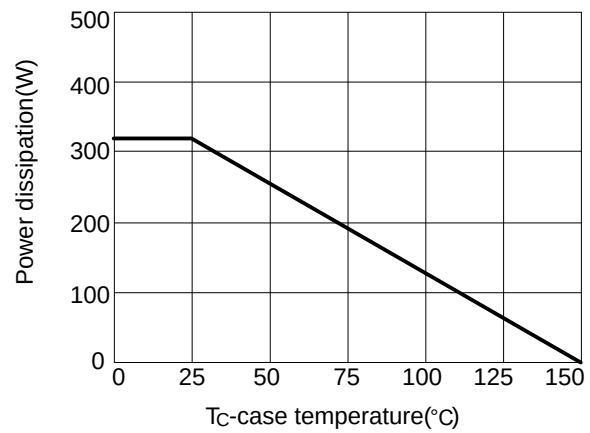


Figure 8: Power de-rating

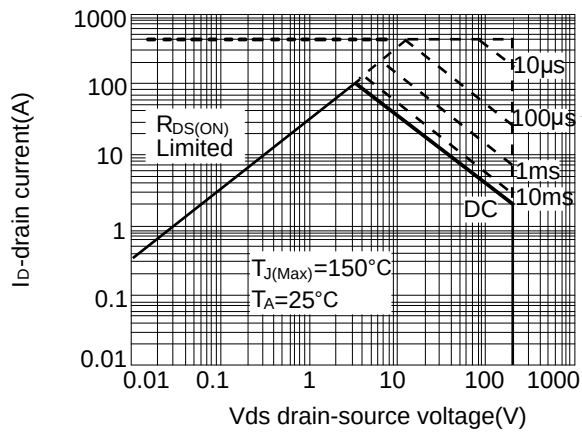


Figure 9: Safe operation area

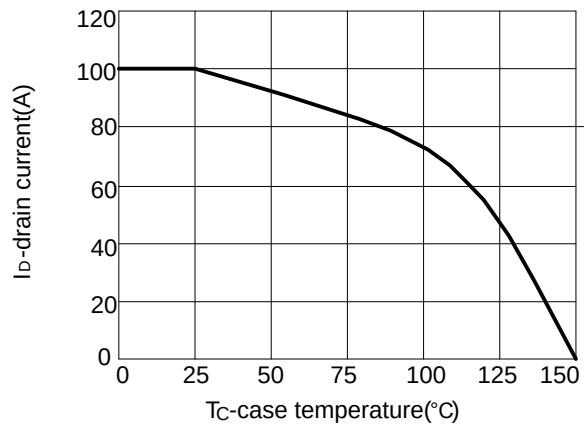
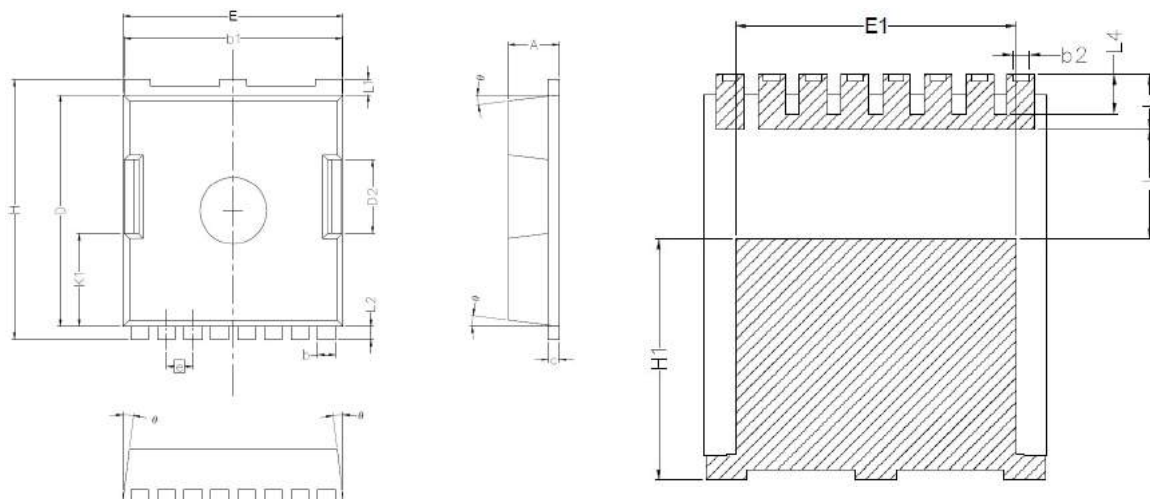


Figure 10: Current de-ratings

■TOLL PACKAGE OUTLINE DIMENSIONS



Symbol	Dimesions In Millimeters	
	Min.	Max.
A	2.20	2.40
b	0.70	0.90
b1	9.70	9.90
b2	0.42	0.50
c	0.40	0.60
D	10.28	10.58
D2	3.10	3.50
E	9.70	10.10
E1	7.90	8.30
e	1.20BSC	
H	11.48	11.88
H1	6.75	7.15
N	8	
J	3.00	3.30
K1	3.98	4.38
L	1.40	1.80
L1	0.60	0.80
L2	0.50	0.70
L4	1.00	1.30
θ	4°	10°